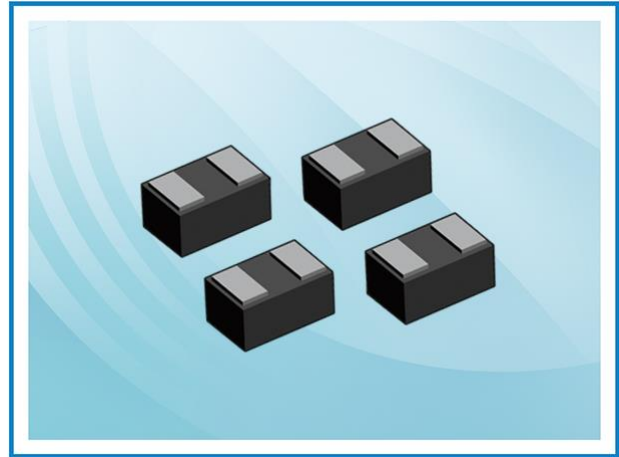


APTUC2421NT – ESD Protection Diode

Feature

- 32 Watts peak pulse power (8/20 μ s)
- Bidirectional configurations
- Solid state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC61000-4-2 (ESD) \pm 20kV (Air), \pm 15kV (Contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)
- IEC61000-4-5 (Lightning): 4A (8/20 μ s)
- AEC-Q101 qualified



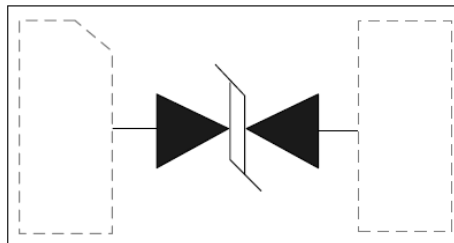
Applications

- Cell Phone Handsets and Accessories
- Micro processor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops and Servers
- Portable Instrumentation

Mechanical Data

- DFN1006 package
- Molding compound flammability rating: UL94 V-0
- Tape and Reel Packaging
- RoHS/WEEE Compliant

Schematic and PIN Configuration



DFN1006

Maximum Rating

Parameter	Symbol	Limit	Unit
IEC61000-4-2 ESD Voltage – Air Mode	$V_{ESD}^{(1)}$	\pm 20	kV
IEC61000-4-2 ESD Voltage – Contact Mode		\pm 15	
Peak Pulse Power	$P_{PP}^{(2)}$	32	W
Peak Pulse Current	$I_{PP}^{(2)}$	4	A
Maximum Lead Solder Temperature (10 seconds duration)	T_L	260	$^{\circ}$ C
Junction Temperature	T_J	-55~125	$^{\circ}$ C
Storage Temperature Range	T_{stg}	-55~125	$^{\circ}$ C

Note:

1. Device stressed with ten non-repetitive ESD pulses.
2. Non-repetitive current pulse 8/20 μ s exponential decay waveform according to IEC61000-4-5.
3. All ratings are measured at environmental temperature of $T_A = 25^{\circ}$ C unless otherwise noted.

APTUC2421NT – ESD Protection Diode

Electrical Characteristics

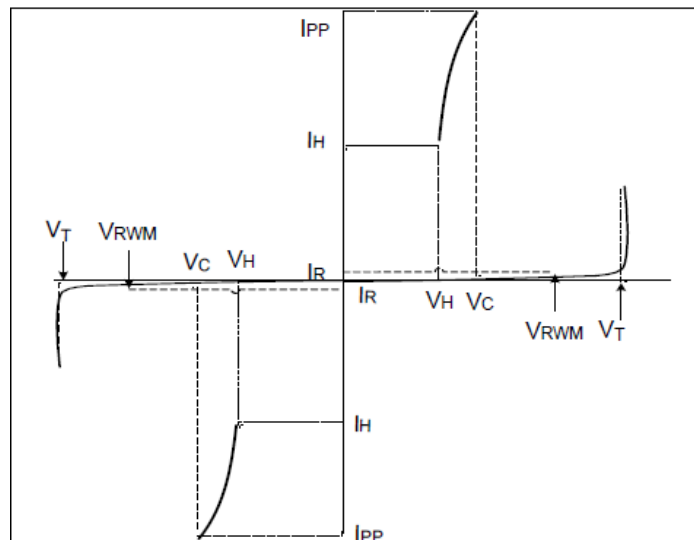
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Stand-off Voltage	$V_{RWM}^{(1)}$				22	V
Holding Voltage	V_H	$I_T = I_H$		3.0		V
Holding Current	I_H		35			mA
Reverse Leakage Current	I_R	$V_{RWM} = 22V$			500	nA
Clamping Voltage	$V_C^{(2)}$	$I_{PP} = 4A$			8.0	V
Trigger Voltage	V_T			24		V
Junction Capacitance	C_J	$V_R = 0V, f = 1MHz$		0.45	0.6	pF

Note:

1. Other voltages available upon request.
2. Non-repetitive current pulse 8/20 μ s exponential decay waveform according to IEC61000-4-5.
3. All ratings are measured at environmental temperature of $T_A = 25^\circ C$ unless otherwise noted.

Electrical Parameters

Symbol	Parameter
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Peak Pulse Current
V_T	Trigger Voltage
I_T	Test Current
I_R	Reverse Leakage Current @ V_{RWM}
V_H	Holding Voltage
I_H	Holding Current



APTUC2421NT – ESD Protection Diode

Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

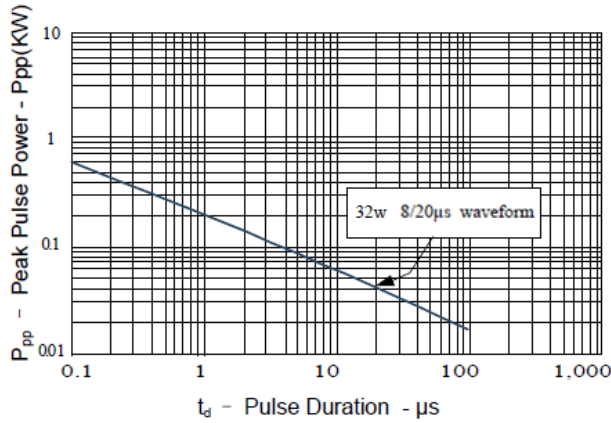


Figure 2: Power Derating Curve

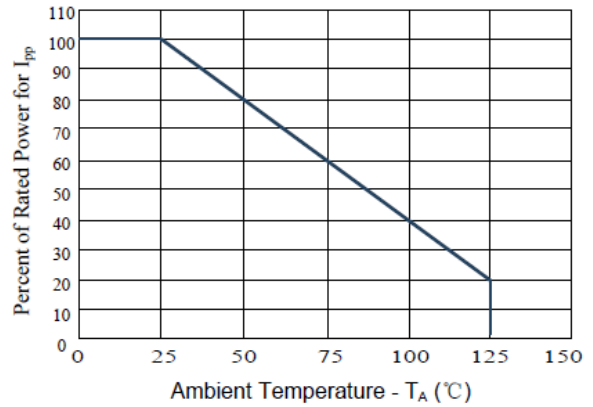


Figure 3: Pulse Waveform

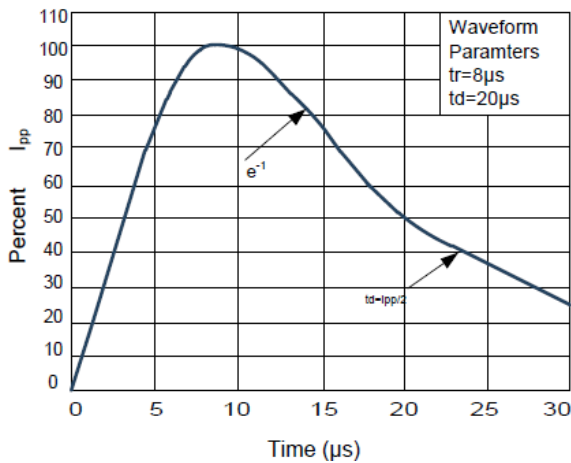


Figure 4: Clamping Voltage vs. Ipp

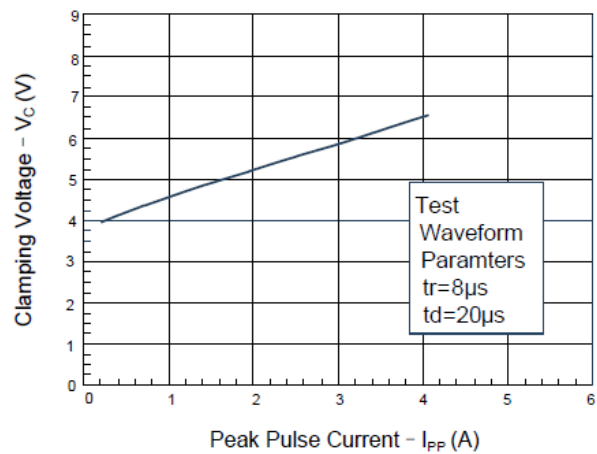


Figure 5: Positive Clamping voltage (TLP)

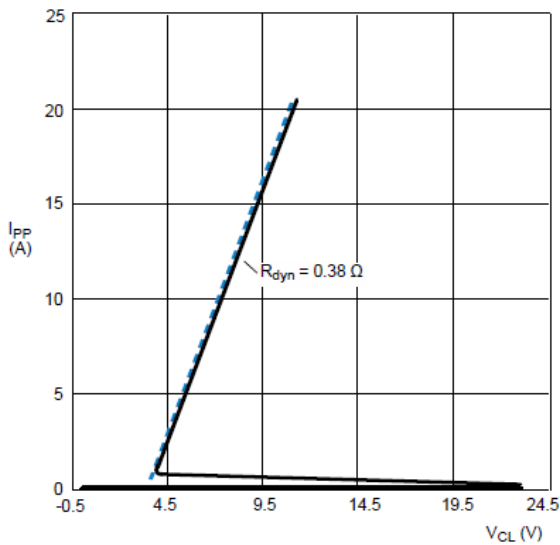
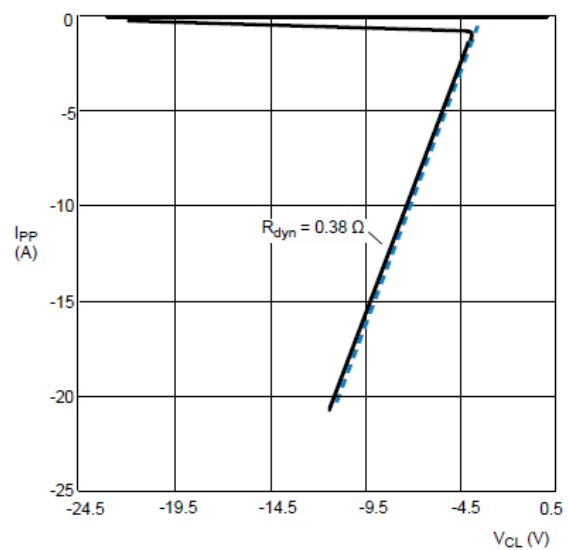
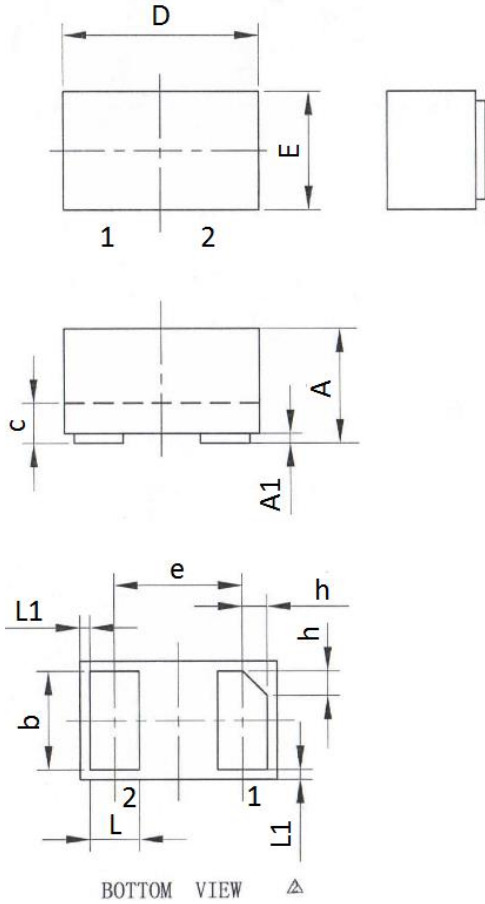


Figure 6: Negative Clamping voltage (TLP)



APTUC2421NT – ESD Protection Diode

DFN1006 Package Outline Dimensions



Symbol	Dimensions (mm)		
	Min	Typ	Max
A	0.45	0.50	0.55
A1	0.00	0.02	0.05
b	0.45	0.50	0.55
c	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65 BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05 REF		
h	0.07	0.12	0.17

Marking

NF

Packaging Information

Order Code	Packaging	Reel Size	PCS/Reel
APTUC2421NT	DFN1006	7 inch	10,000